

SUPPORTING INFORMATION

Efficient synthesis of hierarchical NiO nanosheets for high-performance flexible all-solid-state supercapacitor

Yue Qian,^a Rong Liu,^a Qiufan Wang,^a Jing Xu,^a Di Chen^{*,a} and Guozhen Shen^{*,b}

^a Wuhan National Laboratory for Optoelectronics and School of Optical and Electronic Information, Huazhong University of Science and Technology, Wuhan 430074, China

^b State Key Laboratory for Superlattices and Microstructures, Institute of Semiconductors, Chinese Academy of Sciences, Beijing 100083, China

Address correspondence to dichen@mail.hust.edu.cn; gzshen@semi.ac.cn

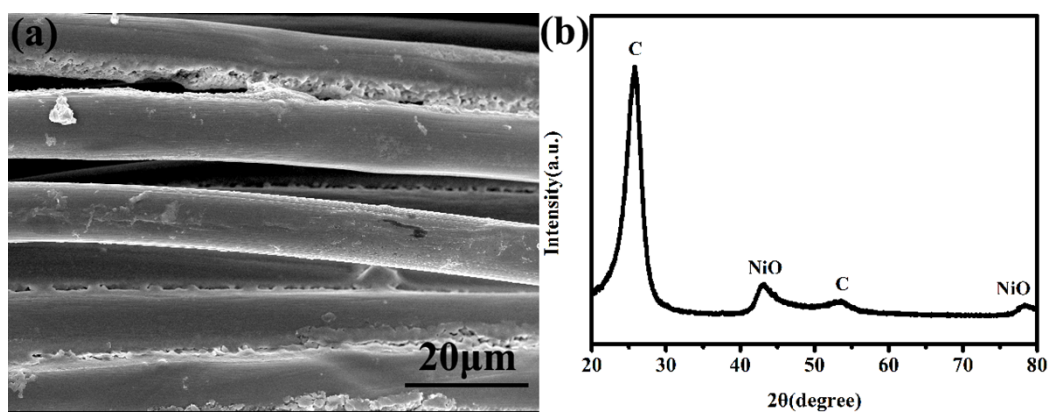


Fig. S1 (a) SEM image of the products obtained in case of no ZnO buffer layer. From this image we can see that it is very hard to grow NiO on bare carbon cloth without ZnO. (b) XRD pattern of the product. The XRD peak from NiO is very weak, further confirming that very few NiO sample was deposited on the carbon cloth.

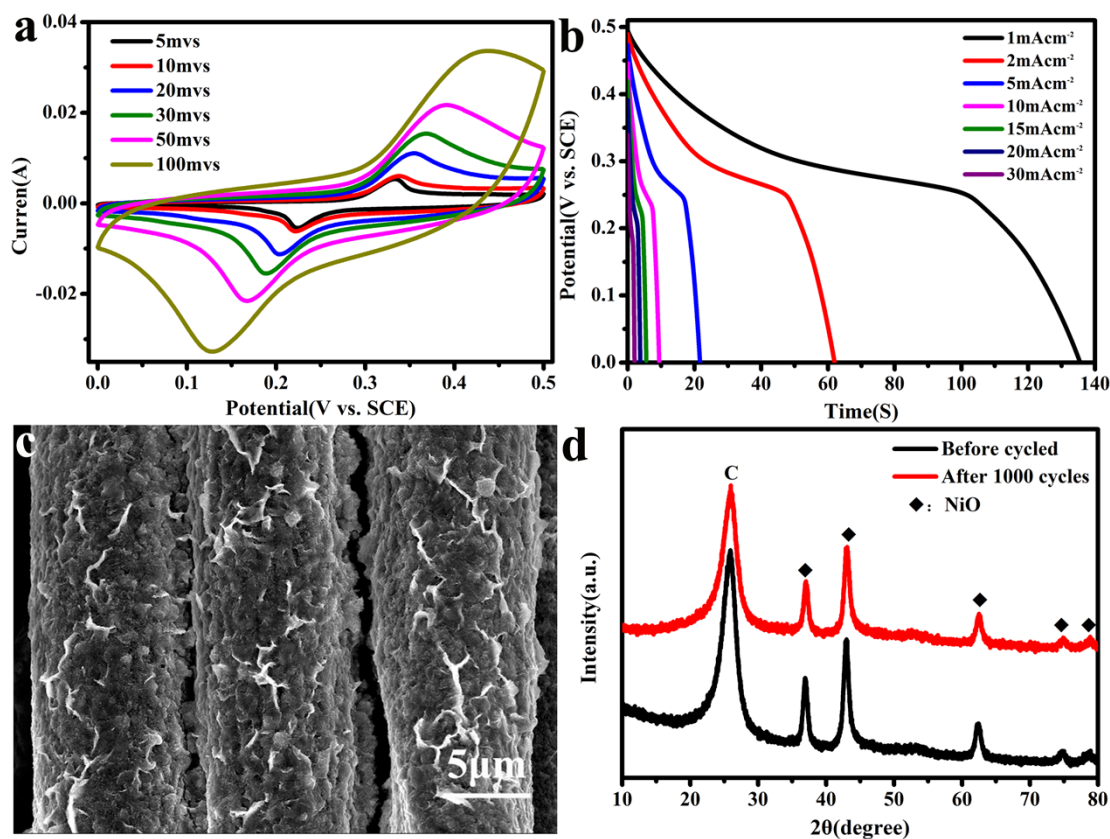


Fig. S2 (a) CV curves of the NiO@ZnO on carbon cloth at different scan rates with potential windows ranging from 0 to 0.5 V. (b) Galvanostatic charge/discharge curves of the NiO@ZnO on carbon cloth at different current densities. (c) SEM image of the NiO@C cloth electrode after 1000 cycles. (d) XRD pattern of the NiO@C cloth before and after cycled 1000 times.